Innokenty I Novikov

List of Publications by Year
in descending order

176	1,498	331259	433756
papers	citations	21 h-index	31 g-index

178	178	178	570
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High power temperature-insensitive 1.3 Âµm InAs/InGaAs/GaAs quantum dot lasers. Semiconductor Science and Technology, 2005, 20, 340-342.	1.0	150
2	MBE-grown metamorphic lasers for applications at telecom wavelengths. Journal of Crystal Growth, 2007, 301-302, 914-922.	0.7	51
3	High-power single mode (>1W) continuous wave operation of longitudinal photonic band crystal lasers with a narrow vertical beam divergence. Applied Physics Letters, 2008, 92, .	1.5	44
4	A 1.33 Âµm InAs/GaAs quantum dot laser with a 46 cm‹sup›â^'1‹/sup›modal gain. Semiconductor Science and Technology, 2008, 23, 105004.	1.0	41
5	Vertical-Cavity Surface-Emitting Lasers Based on Submonolayer InGaAs Quantum Dots. IEEE Journal of Quantum Electronics, 2006, 42, 849-856.	1.0	40
6	High-performance 640-nm-range GaInP-AlGaInP lasers based on the longitudinal photonic bandgap crystal with narrow vertical beam divergence. IEEE Journal of Quantum Electronics, 2005, 41, 1341-1348.	1.0	35
7	6-mW Single-Mode High-Speed 1550-nm Wafer-Fused VCSELs for DWDM Application. IEEE Journal of Quantum Electronics, 2017, 53, 1-8.	1.0	33
8	High-power InAs/GaInAs/GaAs QD lasers grown in a multiwafer MBE production system. Journal of Crystal Growth, 2005, 278, 335-341.	0.7	31
9	Metamorphic 1.5 Âµm-range quantum dot lasers on a GaAs substrate. Semiconductor Science and Technology, 2006, 21, 691-696.	1.0	31
10	Heterostructures for quantum-cascade lasers of the wavelength range of 7â€“8 Î¼m. Technical Physics Letters, 2017, 43, 666-669.	0.2	31
11	High-power singlemode CW operation of 1.5â€…[micro sign]m-range quantum dot GaAs-based laser. Electronics Letters, 2005, 41, 478.	0.5	30
12	Wavelength-stabilized tilted cavity quantum dot laser. Semiconductor Science and Technology, 2004, 19, 1183-1188.	1.0	28
13	Effect of p-Doping of the Active Region on the Temperature Stability of InAsâ•GaAs QD Lasers. Semiconductors, 2005, 39, 477.	0.2	28
14	Degradation-robust single mode continuous wave operation of 1.46Î¼m metamorphic quantum dot lasers on GaAs substrate. Applied Physics Letters, 2006, 89, 041113.	1.5	28
15	High-Power Low-Beam Divergence Edge-Emitting Semiconductor Lasers with 1- and 2-D Photonic Bandgap Crystal Waveguide. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1113-1122.	1.9	27
16	Single mode cw operation of 658nm AlGaInP lasers based on longitudinal photonic band gap crystal. Applied Physics Letters, 2006, 88, 231108.	1.5	24
17	Dual-Frequency Generation in Quantum Cascade Lasers of the 8-Î¼m Spectral Range. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2018, 125, 402-404.	0.2	24
18	Tilted Wave Lasers: A Way to High Brightness Sources of Light. IEEE Journal of Quantum Electronics, 2011, 47, 1014-1027.	1.0	22

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19	Reliability performance of 25 Gbit s^{â^'1} 850 nm vertical-cavity surface-emitting lasers. Semiconductor Science and Technology, 2013, 28, 065010.	1.0	22
20	Room-temperature operation of quantum cascade lasers at a wavelength of 5.8 Î¼m. Semiconductors, 2016, 50, 1299-1303.	0.2	22
21	Progress on single mode VCSELs for data- and tele-communications. Proceedings of SPIE, 2012, , .	0.8	21
22	High-power (>1 W) room-temperature quantum-cascade lasers for the long-wavelength IR region. Quantum Electronics, 2020, 50, 141-142.	0.3	20
23	Room Temperature Lasing of Multi-Stage Quantum-Cascade Lasers at 8 Î¼m Wavelength. Semiconductors, 2018, 52, 1082-1085.	0.2	18
24	Lasing of multiperiod quantum-cascade lasers in the spectral range of (5.6â€“5.8)-Î¼m under current pumping. Semiconductors, 2015, 49, 1527-1530.	0.2	17
25	Room Temperature Lasing of Single-Mode Arched-Cavity Quantum-Cascade Lasers. Technical Physics Letters, 2019, 45, 398-400.	0.2	17
26	QD lasers: physics and applications. , 2005, , .		16
27	Ultrahigh gain and non-radiative recombination channels in 1.5 Âµm range metamorphic InAsâ€“InGaAs quantum dot lasers on GaAs substrates. Semiconductor Science and Technology, 2005, 20, 33-37.	1.0	16
28	High-power high-brightness semiconductor lasers based on novel waveguide concepts. Proceedings of SPIE, 2010, , .	0.8	16
29	Heterostructures of Single-Wavelength and Dual-Wavelength Quantum-Cascade Lasers. Semiconductors, 2018, 52, 745-749.	0.2	16
30	High-Power Quantum-Cascade Lasers Emitting in the 8-Î¼m Wavelength Range. Technical Physics Letters, 2019, 45, 735-738.	0.2	16
31	Narrow vertical beam divergence laser diode based on longitudinal photonic band crystal waveguide. Electronics Letters, 2003, 39, 1729.	0.5	15
32	Waferâ€fused 1300Ânm VCSELs with an active region based on superlattice. Electronics Letters, 2021, 57, 697-698.	0.5	15
33	High Power Single Mode 1300-nm Superlattice Based VCSEL: Impact of the Buried Tunnel Junction Diameter on Performance. IEEE Journal of Quantum Electronics, 2022, 58, 1-15.	1.0	15
34	Lasing in 9.6-Î¼m Quantum Cascade Lasers. Technical Physics, 2018, 63, 1511-1515.	0.2	14
35	High power GaInPâ^•AlGaInP visible lasers (=646â€…nm) with narrow circular shaped far-field pattern. Electronics Letters, 2005, 41, 741.	0.5	13
36	High power GaAsâ^•AlGaAs lasers (Î»â^¼850nm) with ultranarrow vertical beam divergence. Applied Physics Letters, 2006, 89, 231114.	1.5	13

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37	A high-power 975 nm tilted cavity laser with a 0.13 nm K^{â^'1}thermal shift of the lasing wavelength. Semiconductor Science and Technology, 2007, 22, 1061-1065.	1.0	13
38	Low divergence edge-emitting laser with asymmetric waveguide based on one-dimensional photonic crystal. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 919-922.	0.8	12
39	Anomalous dynamic characteristics of semiconductor quantum-dot lasers generating on two quantum states. Technical Physics Letters, 2007, 33, 4-7.	0.2	12
40	High-power one-, two-, and three-dimensional photonic crystal edge-emitting laser diodes for ultra-high brightness applications. Proceedings of SPIE, 2008, , .	0.8	12
41	Optical Gain in Laser Heterostructures with an Active Area Based on an InGaAs/InGaAlAs Superlattice. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2019, 127, 1053-1056.	0.2	12
42	Collective resonance and form factor of homogeneous broadening in semiconductors. Applied Physics Letters, 2000, 76, 2514-2516.	1.5	11
43	Temperature Dependence of the Effective Coefficient of Auger Recombination in 1.3 Î¼m InAsâ•GaAs QD Lasers. Semiconductors, 2005, 39, 481.	0.2	11
44	Turn-on Dynamics of Quantum Cascade Lasers with a Wavelength of 8100 nm at Room Temperature. Technical Physics, 2018, 63, 1656-1658.	0.2	11
45	Continuous-wave Lasing of Single-Mode Metamorphic Quantum Dot Lasers for the 1.5-Î¼m Spectral Region. Semiconductors, 2005, 39, 1415.	0.2	10
46	Wavelength-stabilized tilted wave lasers with a narrow vertical beam divergence. Semiconductor Science and Technology, 2008, 23, 075043.	1.0	10
47	Temperature and current dependences of the lasing spectrumâ€™s width of quantum dot lasers. Semiconductors, 2009, 43, 1597-1601.	0.2	10
48	Temperature characteristics of low-threshold high-efficiency quantum-dot lasers with the emission wavelength from 1.25 to 1.29 Âµm. Semiconductors, 2003, 37, 1239-1242.	0.2	9
49	Longitudinal photonic bandgap crystal laser diodes with ultra-narrow vertical beam divergence. , 2006, , .		9
50	VCSELs based on arrays of sub-monolayer InGaAs quantum dots. Semiconductors, 2006, 40, 615-619.	0.2	9
51	20 Gbit/s error free transmission with ~850 nm GaAs-based vertical cavity surface emitting lasers (VCSELs) containing InAs-GaAs submonolayer quantum dot insertions. Proceedings of SPIE, 2009, , .	0.8	9
52	On the gain properties of â€œthinâ€•elastically strained InGaAs/InGaAlAs quantum wells emitting in the near-infrared spectral region near 1550 nm. Semiconductors, 2016, 50, 1412-1415.	0.2	9
53	Analysis of the Internal Optical Losses of the Vertical-Cavity Surface-Emitting Laser of the Spectral Range of 1.55 Âµm Formed by a Plate Sintering Technique. Optics and Spectroscopy (English Translation) Tj ETQq1 0 1 2 0.784314 rgBT		
54	A Vertical-Cavity Surface-Emitting Laser for the 1.55-Î¼m Spectral Range with Tunnel Junction Based on n++-InGaAs/p++-InGaAs/p++-InAlGaAs Layers. Technical Physics Letters, 2020, 46, 854-858.	0.2	9

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55	The Effect of a Saturable Absorber in Long-Wavelength Vertical-Cavity Surface-Emitting Lasers Fabricated by Wafer Fusion Technology. Technical Physics Letters, 2020, 46, 1257-1262.	0.2	9
56	Improved degradation stability of blue-green II-VI light-emitting diodes with excluded nitrogen-doped ZnSe-based layers. Semiconductors, 2001, 35, 1340-1344.	0.2	8
57	Single transverse mode 850â€…nm GaAs/AlGaAs lasers with narrow beam divergence. Electronics Letters, 2006, 42, 1157.	0.5	8
58	High-power edge-emitting laser diode with narrow vertical beam divergence. Electronics Letters, 2011, 47, 1339.	0.5	8
59	Digital data transmission using electro-optically modulated vertical-cavity surface-emitting laser with saturable absorber. Applied Physics Letters, 2014, 104, .	1.5	8
60	Quantum-Cascade Lasers with a Distributed Bragg Reflector Formed by Ion-Beam Etching. Technical Physics Letters, 2020, 46, 312-315.	0.2	8
61	Heterostructures of Quantum-Cascade Laser for the Spectral Range of 4.6 Î¼m for Obtaining a Continuous-Wave Lasing Mode. Technical Physics Letters, 2020, 46, 442-445.	0.2	8
62	Tilted cavity laser (Critical Review Lecture). , 2004, 5509, 61.		7
63	High-power wavelength stabilized 970nm tilted cavity laser with a 41.3dB side mode suppression ratio. Applied Physics Letters, 2007, 91, 241112.	1.5	7
64	Quantum dot insertions in VCSELs from 840 to 1300 nm: growth, characterization, and device performance. Proceedings of SPIE, 2009, , .	0.8	7
65	Optical properties of InGaAs/InGaAlAs quantum wells for the 1520â€“1580 nm spectral range. Semiconductors, 2016, 50, 1186-1190.	0.2	7
66	Optical Gain of 1550-nm Range Multiple-Quantum-Well Heterostructures and Limiting Modulation Frequencies of Vertical-Cavity Surface-Emitting Lasers Based on Them. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2018, 125, 238-242.	0.2	7
67	Broad-area InAsâ•GaAs quantum dot lasers incorporating Intermixed passive waveguide. Electronics Letters, 2007, 43, 29.	0.5	6
68	The impact of thermal effects on the performance of vertical-cavity surface-emitting lasers based on sub-monolayer InGaAs quantum dots. Semiconductor Science and Technology, 2007, 22, 203-208.	1.0	6
69	A single-spatial-mode semiconductor laser based on InAs/InGaAs quantum dots with a diffraction filter of optical modes. Semiconductors, 2010, 44, 1357-1361.	0.2	6
70	Slow passage through thresholds in quantum dot lasers. Physical Review E, 2016, 94, 052208.	0.8	6
71	Continuous wave and modulation performance of 1550nm band wafer-fused VCSELs with MBE-grown InP-based active region and GaAs-based DBRs. Proceedings of SPIE, 2017, , .	0.8	6
72	High Temperature Laser Generation of Quantum-Cascade Lasers in the Spectral Region of 8 Î¼m. Physics of the Solid State, 2018, 60, 2291-2294.	0.2	6

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73	Vertical-cavity surface-emitting lasers with intracavity contacts and a rhomboidal current aperture for compact atomic clocks. Quantum Electronics, 2019, 49, 187-190.	0.3	6
74	Influence of Output Optical Losses on the Dynamic Characteristics of 1.55-Î¼m Wafer-Fused Vertical-Cavity Surface-Emitting Lasers. Semiconductors, 2019, 53, 1104-1109.	0.2	6
75	Spectral Characteristics of Half-Ring Quantum-Cascade Lasers. Optics and Spectroscopy (English) Tj ETQq1 1 0.784314 rgBT /Overlock	0.2	6
76	10-W 4.6-Î¼m quantum cascade lasers. Quantum Electronics, 2020, 50, 720-721.	0.3	6
77	Superradiance in semiconductors. Semiconductors, 1999, 33, 1309-1314.	0.2	5
78	High brilliance photonic band crystal lasers. , 2006, 6350, 22.		5
79	Edge-emitting InGaAs/GaAs laser with high temperature stability of wavelength and threshold current. Semiconductor Science and Technology, 2010, 25, 045003.	1.0	5
80	High-speed single-mode quantum dot and quantum well VCSELs. Proceedings of SPIE, 2011, , .	0.8	5
81	Dropout dynamics in pulsed quantum dot lasers due to mode jumping. Applied Physics Letters, 2015, 106, 261103.	1.5	5
82	1.55-Î¼m-Range Vertical-Cavity Surface-Emitting Lasers, Manufactured by Wafer Fusion of Heterostructures Grown by Solid-Source Molecular-Beam Epitaxy. Semiconductors, 2020, 54, 1276-1283.	0.2	5
83	850 nm optical components for 25 Gb/s optical fiber data communication links over 100 m at 85Â°C. , 2011, , .		4
84	Influence of optical losses on the dynamic characteristics of linear arrays of near-infrared vertical-cavity surface-emitting lasers. Semiconductors, 2013, 47, 844-848.	0.2	4
85	Degradation-robust 850-nm vertical-cavity surface-emitting lasers for 25Gb/s optical data transmission. Semiconductors, 2014, 48, 77-82.	0.2	4
86	High-speed 1.3 -1.55 um InGaAs/InP PIN photodetector for microwave photonics. Journal of Physics: Conference Series, 2017, 917, 052029.	0.3	4
87	Growth and optical characterization of 7.5 Î¼m quantum-cascade laser heterostructures grown by MBE. Journal of Physics: Conference Series, 2018, 1124, 041029.	0.3	4
88	On the Impact of Barrier-Layer Doping on the Photoluminescence Efficiency of InGaAlAs/InGaAs/InP Strained-Layer Heterostructures. Semiconductors, 2018, 52, 1156-1159.	0.2	4
89	Vertical-Cavity Surface-Emitting 1.55-Î¼m Lasers Fabricated by Fusion. Technical Physics Letters, 2018, 44, 24-27.	0.2	4
90	Lasing of a Quantum-Cascade Laser with a Thin Upper Cladding. Optics and Spectroscopy (English) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	0.2	4

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91	1300-nm wafer-fused VCSELs with InGaAs/InAlGaAs superlattice-based active region. , 2022, , .		4
92	Collective Resonance and Form-Factor of Homogeneous Broadening in Semiconductors. Japanese Journal of Applied Physics, 1999, 38, 4772-4774.	0.8	3
93	Mechanism of dicke superradiance in semiconductor heterostructures. Semiconductors, 2004, 38, 837-841.	0.2	3
94	Edge and surface-emitting tilted cavity lasers (Invited Paper). , 2005, , .		3
95	Modeling of photonic-crystal-based high-power high-brightness semiconductor lasers. , 2010, , .		3
96	Metamorphic distributed Bragg reflectors for the 1440â€“1600 nm spectral range: Epitaxy, formation, and regrowth of mesa structures. Semiconductors, 2015, 49, 1388-1392.	0.2	3
97	Optical characterization of mid-infrared range quantum-cascade laser structures grown by MBE. Journal of Physics: Conference Series, 2017, 917, 052019.	0.3	3
98	Spectral Shift of Quantum-Cascade Laser Emission under the Action of Control Voltage. Technical Physics Letters, 2019, 45, 1136-1139.	0.2	3
99	Optically pumped non-zero field magnetometric sensor for the magnetoencephalographic systems using intra-cavity contacted VCSELs with rhomboidal oxide current aperture. Journal of Physics: Conference Series, 2020, 1697, 012175.	0.3	3
100	Observation of Long Turn-On Delay in Pulsed Quantum Cascade Lasers. Journal of Lightwave Technology, 2022, 40, 2104-2110.	2.7	3
101	1.3 Î¼m optically-pumped monolithic VCSEL based on GaAs with InGa(Al)As superlattice active region. Laser Physics Letters, 2022, 19, 075801.	0.6	3
102	Collective resonances and shape function for homogeneous broadening of the emission spectra of quantum-well semiconductor heterostructures. Semiconductors, 1999, 33, 779-781.	0.2	2
103	1.3-1.5 Î¼m quantum dot lasers on foreign substrates: growth using defect reduction technique, high-power CW operation, and degradation resistance. , 2006, , .		2
104	Experimental study of temperature dependence of threshold characteristics in semiconductor VCSELs based on submonolayer InGaAs QDs. Semiconductors, 2006, 40, 1232-1236.	0.2	2
105	MBE-grown ultra-large aperture single-mode vertical-cavity surface-emitting laser with all-epitaxial filter section. Journal of Crystal Growth, 2007, 301-302, 945-950.	0.7	2
106	High-gain injection quantum-dot lasers operating at wavelengths above 1300 nm. Technical Physics Letters, 2008, 34, 1008-1010.	0.2	2
107	Single-Lobe Single-Wavelength Lasing in Ultrabroad-Area Vertical-Cavity Surface-Emitting Lasers Based on the Integrated Filter Concept. IEEE Journal of Quantum Electronics, 2008, 44, 724-731.	1.0	2
108	A temperature-stable semiconductor laser based on coupled waveguides. Semiconductors, 2011, 45, 550-556.	0.2	2

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109	Design concepts of monolithic metamorphic vertical-cavity surface-emitting lasers for the 1300â€“1550 nm spectral range. Semiconductors, 2015, 49, 1522-1526.	0.2	2
110	Optical properties of metamorphic GaAs/InAlGaAs/InGaAs heterostructures with InAs/InGaAs quantum wells, emitting light in the 1250â€“1400-nm spectral range. Semiconductors, 2016, 50, 612-615.	0.2	2
111	Lasing of metamorphic hybrid 1300nm spectral band VCSEL under optical pumping up to 120 Â°C. , 2017, , .		2
112	Optical properties of metamorphic hybrid heterostuctures for vertical-cavity surface-emitting lasers operating in the 1300-nm spectral range. Semiconductors, 2017, 51, 1127-1132.	0.2	2
113	The Influence of Cavity Design on the Linewidth of Near-IR Single-Mode Vertical-Cavity Surface-Emitting Lasers. Technical Physics Letters, 2018, 44, 28-31.	0.2	2
114	Quantum-Cascade Lasers with U-Shaped Resonator: Single Frequency Generation at Room Temperature. , 2019, , .		2
115	Generation of Frequency Combs by Quantum Cascade Lasers Emitting in the 8-Î¼m Wavelength Range. Technical Physics Letters, 2019, 45, 1027-1030.	0.2	2
116	Effect of coherent population trapping in a compact microfabricated Cs gas cell pumped by intra-cavity contacted VCSELs with rhomboidal oxide current aperture. Journal of Physics: Conference Series, 2019, 1400, 077014.	0.3	2
117	Tunable single-frequency source based on a DFB laser array for the spectral region of 1.55 Î¼m. Quantum Electronics, 2019, 49, 1158-1162.	0.3	2
118	Spectral Dynamics of Quantum Cascade Lasers Generating Frequency Combs in the Long-Wavelength Infrared Range. Technical Physics, 2020, 65, 1281-1284.	0.2	2
119	The Influence of the Parameters of a Short-Period InGaAs/InGaAlAs Superlattice on Photoluminescence Efficiency. Technical Physics Letters, 2020, 46, 1128-1131.	0.2	2
120	Design of the New Control System for Linac-200. Physics of Particles and Nuclei Letters, 2020, 17, 600-603.	0.1	2
121	Dynamics of Frequency Combs Generation by QCLs in 8 Î¼m Wavelength Range. , 2020, , .		2
122	Surface Emitting Quantum-Cascade Ring Laser. Semiconductors, 2021, 55, 591.	0.2	2
123	Degradation of NSe-Free Blue-Green ZnSe-Based Light Emitting Diodes with Superlattice Miniband Hole Transport. Physica Status Solidi (B): Basic Research, 2002, 229, 1019-1023.	0.7	1
124	Generation of superradiation in quantum dot nanoheterostructures. Semiconductors, 2008, 42, 714-719.	0.2	1
125	Efficient electro-optic semiconductor medium based on type-II heterostructures. Semiconductors, 2013, 47, 1528-1538.	0.2	1
126	The effect of slow passage in the pulse-pumped quantum dot laser. , 2014, , .		1

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127	MBE growth and characterization of InAlAs/InGaAs 9 Î¼m range quantum cascade laser. Journal of Physics: Conference Series, 2017, 917, 052016.	0.3	1
128	Phosphorus-free mode-locked semiconductor laser with emission wavelength 1550 nm. Journal of Physics: Conference Series, 2017, 917, 052021.	0.3	1
129	Dual-band generation around 8 Î¼m by quantum cascade lasers in wide temperature range. Journal of Physics: Conference Series, 2018, 1135, 012073.	0.3	1
130	Quantum-cascade lasers of mid-IR spectral range: epitaxy, diagnostics and device characteristics. EPJ Web of Conferences, 2018, 195, 04001.	0.1	1
131	Quantum-cascade lasers in the 7-8 Î¼m spectral range with full top metallization. Journal of Physics: Conference Series, 2018, 993, 012031.	0.3	1
132	Mode-Locked Lasers with â€œThinâ€•Quantum Wells in 1.55 Î¼m Spectral Range. Technical Physics Letters, 2018, 44, 174-177.	0.2	1
133	Temperature Dependence of the Parameters of 1.55-Î¼m Semiconductor Lasers with Thin Quantum Wells Based on Phosphorus-Free Heterostructures. Technical Physics Letters, 2019, 45, 549-552.	0.2	1
134	Spontaneous Emission and Lasing of a Two-Wavelength Quantum-Cascade Laser. Semiconductors, 2019, 53, 345-349.	0.2	1
135	High-power Î» = 8 Âµm quantum-cascade lasers at room temperature. Journal of Physics: Conference Series, 2019, 1400, 066048.	0.3	1
136	High-coupling distributed feedback lasers for the 1.55 Î¼m spectral region. Quantum Electronics, 2019, 49, 801-803.	0.3	1
137	Study of the Spectra of Arched-Cavity Quantum-Cascade Lasers. Optics and Spectroscopy (English) Tj ETQq1 1 0.784314 rgBT /Overl	0.2	1
138	Influence of the doping type on the temperature dependencies of the photoluminescence efficiency of InGaAlAs/InGaAs/InP heterostructures. Journal of Luminescence, 2021, 239, 118393.	1.5	1
139	Quantum-Cascade Ring Resonator Laser with 7â€“8 Î¼m Wavelength and Surface Radiation Output. Semiconductors, 2020, 54, 1816-1819.	0.2	1
140	A Study of the Spatial-Emission Characteristics of Quantum-Cascade Lasers for the 8-Î¼m Spectral Range. Technical Physics Letters, 2020, 46, 1152-1155.	0.2	1
141	The Technique for QCLs Heating Dynamics Mesurements. , 2020, , .		1
142	Characterization of lasing regimes of 1.3â€‰â€‰Âµm vertical-cavity surface-emitting lasers based on a short-period InGaAs/InGaAlAs superlattice. Journal of Optical Technology (A Translation of) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 150 137 Td	0.2	1
143	Treatment of inhomogeneous radiation broadening in quantum dot heterostructures described within the framework of the superradiation model. Technical Physics Letters, 2000, 26, 259-261.	0.2	0
144	Waveguide InGaAsP/InP photodetectors for low-power autocorrelation measurements at 1.55 Âµm. Semiconductors, 2002, 36, 714-716.	0.2	0

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145	Electroluminescence of injection lasers based on vertically coupled quantum dots near the lasing threshold. Semiconductors, 2003, 37, 112-114.	0.2	0
146	Two-photon absorption in InGaAsP waveguides. , 2003, , .		0
147	Peculiarities of electroluminescence of quantum dot laser heterostructures. , 2003, 5036, 67.		0
148	Superradiance as a transition phase from spontaneous to stimulated emission in low-dimensional semiconductor heterostructures. , 2003, , .		0
149	Electroluminescent studies of emission characteristics of InGaAsN/GaAs injection lasers in a wide temperature range. Semiconductors, 2004, 38, 727-731.	0.2	0
150	Competition Of Different Recombination Channels In Metamorphic 1.5 Î¼m Range Quantum Dot Lasers On GaAs Substrate. AIP Conference Proceedings, 2007, , .	0.3	0
151	Tilted cavity concept for the high-power wavelength stabilized diode lasers. , 2008, , .		0
152	Quantum dot semiconductor lasers of the 1.3 Î¼m wavelength range with high temperature stability of the lasing wavelength (0.2 nm/K). Semiconductors, 2009, 43, 680-684.	0.2	0
153	Dynamical interplay between ground and excited states in quantum dot laser. , 2014, , .		0
154	Evidence of negative electrorefraction in type-II GaAs/GaAlAs short-period superlattice. Semiconductor Science and Technology, 2015, 30, 115013.	1.0	0
155	Impact of the carrier relaxation paths on two-state operation in quantum dot lasers. , 2015, , .		0
156	1550â€...nm mode-locked semiconductor lasers for all-optical analog-to-digital conversion. AIP Conference Proceedings, 2017, , .	0.3	0
157	The concept for realization of quantum-cascade lasers emitting at 7.5 Î¼m wavelength. Journal of Physics: Conference Series, 2017, 929, 012082.	0.3	0
158	Semiconductor light sources for near- and mid-infrared spectral ranges. Journal of Physics: Conference Series, 2017, 917, 022003.	0.3	0
159	Molecular-beam epitaxy of 7-8 Î¼m range quantum-cascade laser heterostructures. Journal of Physics: Conference Series, 2017, 929, 012081.	0.3	0
160	Quantum-cascade lasers of 8-9 Î¼m spectral range. , 2018, , .		0
161	Effect of barrier doping on photoluminescence of 1550 nm range multi quantum well heterostructures.. , 2018, , .		0
162	A heterostructure for resonant-cavity GaAs p-i-n photodiode with 840-860 nm wavelength. Journal of Physics: Conference Series, 2019, 1236, 012071.	0.3	0

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163	Temperature performance of InGaAs/InGaAlAsTemperature performance of InGaAs/InGaAlAs laser diodes with Î´-doping active region. Journal of Physics: Conference Series, 2019, 1410, 012104.	0.3	0
164	Observation of the increase in turn-on delay of quantum cascade lasers under pulsed electrical pumping with finite rise time. Journal of Physics: Conference Series, 2020, 1697, 012062.	0.3	0
165	Investigation of optical and structural properties of three-dimensional InGaPAs islands formed by substitution of elements of the fifth group. Journal of Physics: Conference Series, 2020, 1697, 012106.	0.3	0
166	Turn-on delay in the mid-infrared quantum-cascade lasers: experiment and numerical simulations. , 2021, , .		0
167	Optical Properties of Three-Dimensional InGaP(As) Islands Formed by Substitution of Fifth-Group Elements. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2021, 129, 256-260.	0.2	0
168	High-Power (>13 W) Quantum-Cascade Lasers for Long Wavelength Infrared Range. , 2020, , .		0
169	Vertical cavity surface emitting laser of 1.55 Î¼m spectral range, manufactured by molecular beam epitaxy and wafer fusion technique. Journal of Physics: Conference Series, 2020, 1697, 012178.	0.3	0
170	Effect of saturable absorber in 1.5 Î¼m wafer-fused vertical cavity surface-emitting lasers. Journal of Physics: Conference Series, 2020, 1697, 012167.	0.3	0
171	1.55 Âµm range edge-emitting laser diodes based on InGaAs/InGaAlAs superlattice and InGaAs quantum wells. Journal of Physics: Conference Series, 2020, 1695, 012072.	0.3	0
172	Turn-on Delay of Quantum Cascade Lasers under Pulsed Pumping with Non-zero Rise-time. , 2020, , .		0
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